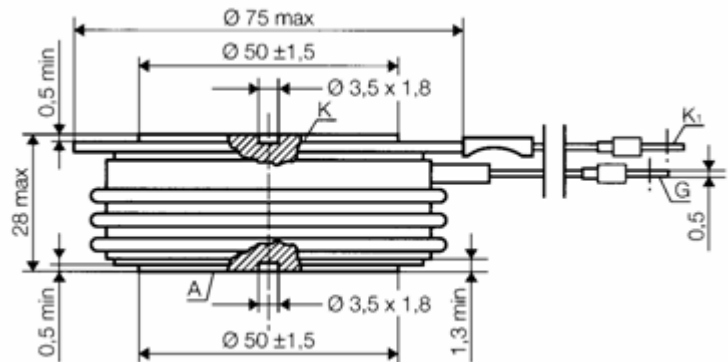


I _L	Latching current	A	15	T _{vj} =25°C; U _D =12V, Gate pulse: 10V, 5Ω, 1μs rise time, 10μs
I _H	Holding current	A	1,0	T _{vj} =25°C; U _D =12, Gate open
U _{GT}	Gate trigger direct voltage	V	2,5	T _{vj} =25°C; U _D =12V
I _{GT}	Gate trigger direct current	A	0,3	T _{vj} =25°C; U _D =12V
U _{GD}	Gate non-trigger direct voltage	V	0,25	T _{vj} =125°C; U _D =0,67 U _{DRM}
t _{gd}	Delay time	μs	2,5	T _{vj} =25°C, U _D =500V, I _{TM} =1000A Gate pulse: 10V, 5Ω, 1μs rise time, 10μs
t _{gt}	Turn-on time	μs	4,0	
t _q	Turn-off time	μs	16÷25 20÷32	T _{vj} =125°C, I _{TM} =1000A, di _R /dt= 10 A/μs U _R =100V U _D =0,67 U _{DRM} Di _D /dt= 50 A/μs Di _D /dt= 200 A/μs
Q _{rr}	Recovered charge	μC	350	T _{vj} =125°C, I _{TM} =1000A, di _R /dt= 50 A/μs, U _R =100V
(di _D /dt) cr	Critical rate of rise of off-state voltage	V/μs	500 1000	T _{vj} =125°C; U _D =0,67 U _{DRM} Gate open
R _{thjc}	Thermal resistance junction to case	°C/W	0,021	Direct current, double side cooled

Mounting force : 19 – 28 kN
Weight : 580 gram



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